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BLS9G2729L-350: BLS9G2729LS-350 LDMOS S-band radar power transistor

AMPLEON

Rev. 1 — 13 April 2017

Product data sheet

Product profile

1.1 General description

350 W LDMOS power transistor for S-band applications in the frequency range from 2.7 GHz to 2.9 GHz.

Test information Table 1.

Typical RF performance at T_{case} = 25 °C; t_{p} = 300 μ s; δ = 10 %; I_{Dq} = 400 mA; in a class-AB demo circuit.

Test signal	f	V _{DS}	P_L	G _p	η_{D}
	(GHz)	(V)	(W)	(dB)	(%)
pulsed RF	2.7 to 2.9	28	320	14	50

1.2 Features and benefits

- High efficiency
- Excellent ruggedness
- Designed for S-band operations
- Excellent thermal stability
- Easy power control
- Integrated dual sided ESD protection enables excellent off-state isolation
- High flexibility with respect to pulse formats
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

■ S-band radar applications in the frequency range from 2.7 GHz to 2.9 GHz

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLS9G2729	L-350 (SOT502A)		
1	drain		
2	gate	5 1 5	1
3	source [1]		2 - 3 3 sym112
BLS9G2729	DLS-350 (SOT502B)		
1	drain		
2	gate	1 3	1
3	source [1]	2	2 - 3 sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage				
	Name	Name Description				
BLS9G2729L-350	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT502A			
BLS9G2729LS-350	-	earless flanged ceramic package; 2 leads	SOT502B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-6	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

Thermal characteristics 5.

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$Z_{\text{th(j-mb)}}$	transient thermal impedance from junction to	T _{case} = 85 °C; P _L = 350 W		
	mounting base	t_p = 100 μ s; δ = 10 %	0.07	K/W
		t_p = 200 µs; δ = 10 %	0.09	K/W
		t_p = 300 μ s; δ = 10 %	0.11	K/W
		t_p = 100 μ s; δ = 20 %	0.09	K/W

Characteristics 6.

Table 6. **DC** characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V; } I_D = 4.5 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 450 mA	1.5	2	2.5	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	85	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	400	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 450 A	-	4.2	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 15.75 A$	-	0.030	-	Ω

RF characteristics

Test signal: pulsed RF; t_p = 300 μ s; δ = 10 %; RF performance at V_{DS} = 28 V; I_{Da} = 400 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 320 W	12	14	-	dB
RLin	input return loss	P _L = 320 W	-	-10	-	dB
η_{D}	drain efficiency	P _L = 320 W	45	50	-	%
P _{droop(pulse)}	pulse droop power	P _L = 320 W	-	0.0	0.3	dB
t _r	rise time	P _L = 320 W	-	6	50	ns
t _f	fall time	P _L = 320 W	-	6	50	ns
P _{L(2dB)}	output power at 2 dB gain compression		-	350	-	W

Test information 7.

7.1 Ruggedness in class-AB operation

The BLS9G2729L-350 and BLS9G2729LS-350 are capable of withstanding a load mismatch corresponding to VSWR = 10:1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 400 mA; P_L = 320 W; t_p = 300 μ s; δ = 10 %.

7.2 Impedance information

Table 8. Typical impedance

f	Z _S	Z_L
(GHz)	(Ω)	(Ω)
2.7	1.6 – j5.8	1.6 – j3.7
2.8	2.9 – j6.6	1.8 – j3.6
2.9	8.0 – j4.7	2.2 – j3.1

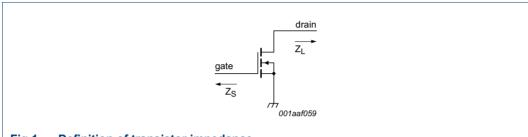


Fig 1. Definition of transistor impedance

7.3 Test circuit

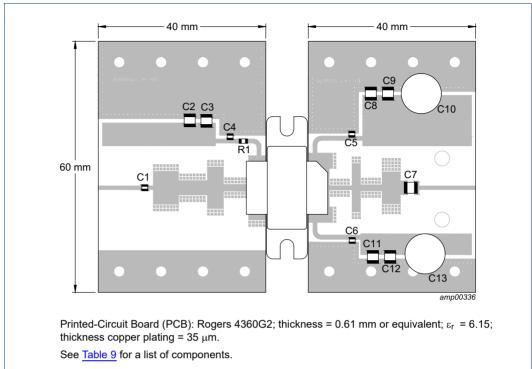
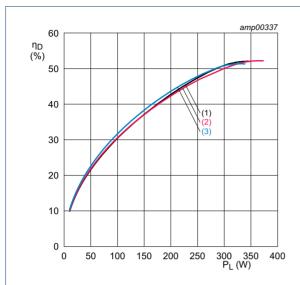


Fig 2. Component layout

Table 9.List of componentsSee Figure 2 for component layout.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	12 pF	ATC800A
C2, C8, C11	multilayer ceramic chip capacitor	1 nF	ATC800B
C3, C9, C12	multilayer ceramic chip capacitor	10 μF	Murata: GRM55DR61H106KA88L
C4, C6, C6	multilayer ceramic chip capacitor	15 pF	ATC800A
C7	multilayer ceramic chip capacitor	12 pF	ATC800B
C10, C13	electrolytic capacitor	100 μF, 63 V	
R1	SMD resistor	5 Ω	0603

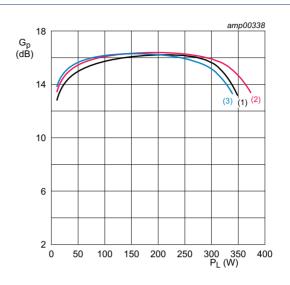
7.4 Graphical data



 V_{DS} = 28 V; I_{Dq} = 400 mA; t_p = 300 μ s; δ = 10 %.

- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz

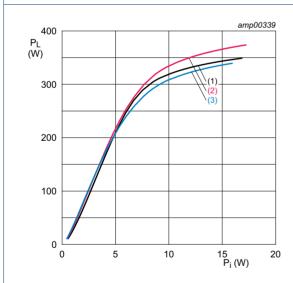
Fig 3. Drain efficiency as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 400 mA; t_p = 300 $\mu s;$ δ = 10 %.

- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz

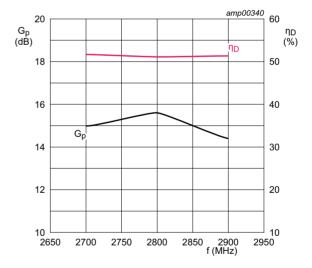
Fig 4. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 400 mA; t_p = 300 $\mu s; \, \delta$ = 10 %.

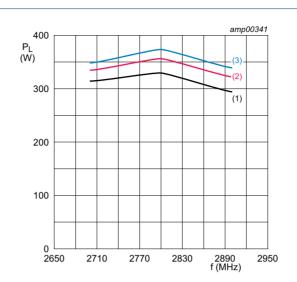
- (1) f = 2700 MHz
- (2) f = 2800 MHz
- (3) f = 2900 MHz

Fig 5. Output power as a function of input power; typical values



 V_{DS} = 28 V; I_{Dq} = 400 mA; P_L = 320 W; t_p = 300 $\mu s;$ δ = 10 %.

Fig 6. Power gain and drain efficiency as function of frequency; typical values



 V_{DS} = 28 V; I_{Dq} = 400 mA; t_p = 300 $\mu s; \, \delta$ = 10 %.

- (1) at P_{L(1dB)}
- (2) at P_{L(2dB)}
- (3) at P_{L(3dB)}

Fig 7. Output power as a function of frequency; typical values

8. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT502A

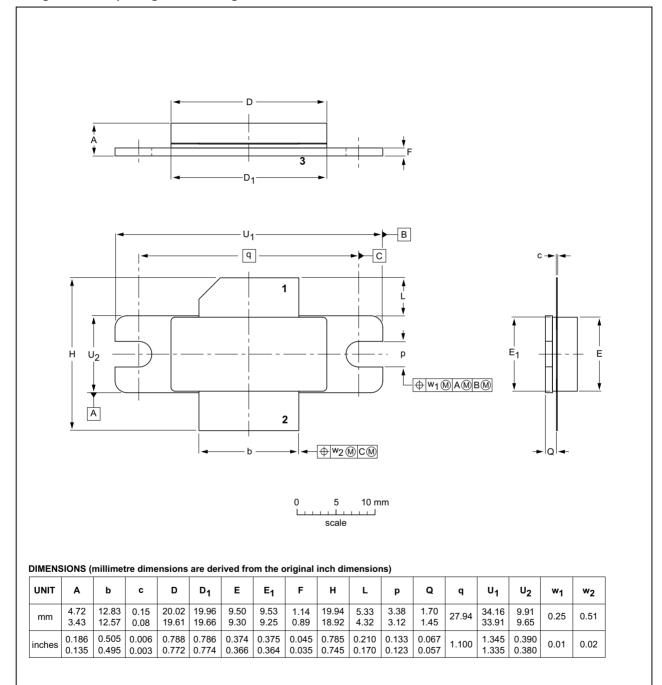


Fig 8. Package outline SOT502A

IEC

OUTLINE

VERSION

SOT502A

JEITA

REFERENCES

JEDEC

ISSUE DATE

03-01-10

12-05-02

EUROPEAN

PROJECTION

Earless flanged ceramic package; 2 leads

SOT502B

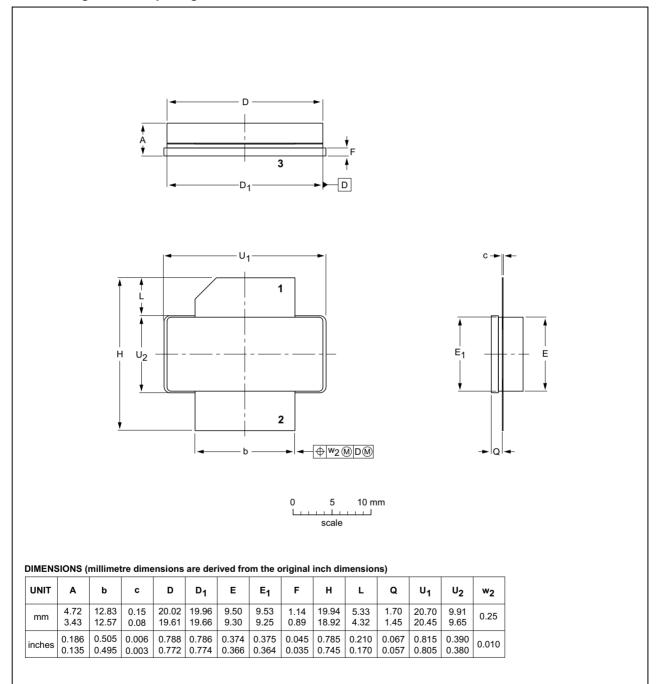


Fig 9. Package outline SOT502B

IEC

OUTLINE

VERSION

SOT502B

JEITA

REFERENCES

JEDEC

ISSUE DATE

07-05-09

12-05-02

EUROPEAN

PROJECTION

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
S-band	Short wave band
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLS9G2729L-350_2729LS-350 v.1	20170413	Product data sheet		-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BLS9G2729L(S)-350

LDMOS S-band radar power transistor

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LDMOS S-band radar power transistor

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